



For Immediate Release

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IXYS Introduces New GaN High Performance RF Power Amplifier For Wireless Applications

Fremont, CA, January 29, 2009 - IXYS Corporation (NASDAQ: IXYS) announced that its Microwave Technology, Inc. (MWT) division has introduced a family of three high linearity and high efficiency RF power amplifier products with output power up to 10 watts based on advanced high quality GaN device technology. The power amplifiers are MGA-242740-02, MGA-495922-02, and MGA-4959-02, targeted at 802.16d/e WiMax applications and 802.11 WLAN related applications with three frequencies bands, 2.4 – 2.7 GHz, 3.3 - 3.8 GHz, 4.9 – 5.9 GHz, respectively. All three parts have high output power of 10Watt (40 dBm) measured at 3 dB gain compression point and linear power gain range from 12 – 15 dB. These GaN based RF power amplifier parts have achieved extraordinary 23% power added efficiency at 2W (33dBm) linear power (burst power) with 2.5% EVM (Error-Vector-Magnitude) under the 64 QAM 802.16 WiMax digital signal modulation scheme.

“The linear power efficiency performance achieved by those GaN based power amplifiers is exceptional and is more than twice, in comparison with the GaAs or Silicon LDMOS based PA counter parts. We have demonstrated the excellent suitability of GaN based power devices for the applications we target and also the advanced microwave/RF amplifier design capabilities of our company,” commented by Dr. Greg Zhou, general manager of MWT. “We will continue to leverage the advantages of the microwave/RF GaN power device technology with high reliability and expand the product family to other applications that demand high linear power and power added efficiency performances including military and high rel applications.”

The GaN based power amplifiers, biased at 28V on drain with quiescent current between 80 – 300 mA, are available in various packages including the low cost surface mount 02 packages. The MTBF (mean-Time-Before-Failure) for those GaN based microwave/RF power amplifiers is over 100 years at 85C ambient temperature. The evaluation boards for the power amplifiers in 02 packages are available now. For detailed datasheets of GaN based power amplifiers and other MWT products please go to MWT's web site www.mwtinc.com. Contact factory at @mwtinc.com or call 510-651-6700 for sample request and price quote.

About IXYS Corporation

IXYS Corporation makes and markets technology-driven products to improve power conversion efficiency, generate solar and wind power and provide efficient motor control for industrial applications. IXYS offers a diversified product base that addresses worldwide needs for power control, electrical efficiency, renewable energy, telecommunications, medical devices, electronic displays and RF power.

Safe Harbor Statement

Any statements contained in this press release that are not statements of historical fact, including the performance, rating, availability, reliability and suitability of products for various applications, may be deemed to be forward-looking statements. There are a number of important factors that could cause the results of IXYS to differ materially from those indicated by these forward-looking statements, including, among others, risks detailed from time to time in the Company's SEC reports, including its Form 10-Q for the quarter ended September 30, 2008. The Company undertakes no obligation to publicly release the results of any revisions to these forward-looking statements.